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MOSFETs Silicon N-Channel MOS (π -MOSVII)

TK4P55DA

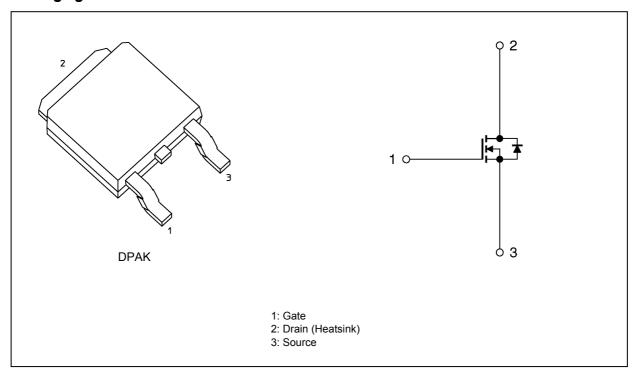
1. Applications

• Switching Voltage Regulators

2. Features

- (1) Low drain-source on-resistance : $R_{DS(ON)} = 2.0 \Omega$ (typ.)
- (2) High forward transfer admittance : $|Y_{fs}| = 1.8 \text{ S (typ.)}$
- (3) Low leakage current : I_{DSS} = 10 μA (max) (V_{DS} = 550V)
- (4) Enhancement mode : V_{th} = 2.4 to 4.4 V (V_{DS} = 10 V, I_{D} = 1 mA)

3. Packaging and Internal Circuit





4. Absolute Maximum Ratings (Note) (Ta = 25 °C unless otherwise specified)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	550	V
Gate-source voltage	,	V_{GSS}	±30	
Drain current (DC)	(Note 1)	I _D	3.5	Α
Drain current (pulsed)	(Note 1)	I _{DP}	14	
Power dissipation (T _c	= 25 °C)	P_{D}	80	W
Single-pulse avalanche energy	(Note 2)	E _{AS}	121	mJ
Avalanche current	(Note 3)	I _{AR}	3.5	Α
Repetitive avalanche energy	(Note 3)	E _{AR}	8	mJ
Reverse drain current (DC)	(Note 1)	I _{DR}	3.5	Α
Reverse drain current (pulsed)	(Note 1)	I _{DRP}	14	
Channel temperature		T _{ch}	150	°C
Storage temperature		T _{stg}	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	R _{th(ch-c)}	1.56	°C/W
Channel-to-ambient thermal resistance	R _{th(ch-a)}	125	

Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2: V_{DD} = 90 V, T_{ch} = 25 °C (initial), L = 17.1 mH, R_G = 25 Ω , I_{AR} = 3.5 A

Note 3: Repetitive rating; pulse width limited by maximum channel temperature.

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±1	μΑ
Drain cut-off current	I _{DSS}	V _{DS} = 550 V, V _{GS} = 0 V	_	_	10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	550		_	V
Gate threshold voltage	V_{th}	V _{DS} = 10 V, I _D = 1 mA	2.4		4.4	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 10 V, I _D = 1.8 A	_	2.0	2.45	Ω
Forward transfer admittance	Y _{fs}	V _{DS} = 10 V, I _D = 1.8 A	0.4	1.8	_	S

6.2. Dynamic Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 25 V, V _{GS} = 0 V,	_	380		pF
Reverse transfer capacitance	C_{rss}]f = 1 MHz	_	2.5		
Output capacitance	C _{oss}		_	45	_	
Switching time (rise time)	t _r	See Fig.6.2.1	_	15	_	ns
Switching time (turn-on time)	t _{on}		_	35	_	
Switching time (fall time)	t _f		_	7	_	
Switching time (turn-off time)	t _{off}		-	55		

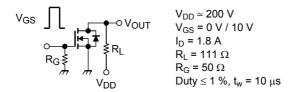


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	9	$V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V},$	_	9	_	nC
Gate-source charge	Q_{gs}	I _D = 3.5 A	_	5	_	
Gate-drain charge	Q_{gd}		_	4	_	

6.4. Source-Drain Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	V_{DSF}	I _{DR} = 3.5 A, V _{GS} = 0 V	_	_	-1.7	V
Reverse recovery time	t _{rr}	I _{DR} = 3.5 A, V _{GS} = 0 V,	_	800	_	ns
Reverse recovery charge	Q _{rr}	-di/dt = 100 A/μs	_	4.4	_	μС



7. Marking

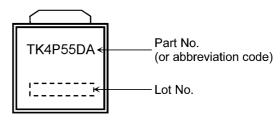


Fig. 7.1 Marking

8. Characteristics Curves (Note)

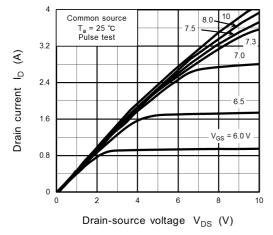


Fig. 8.1 $I_D - V_{DS}$

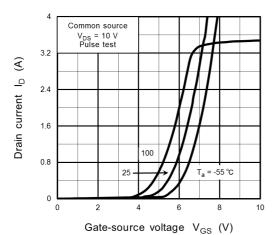


Fig. 8.3 I_D - V_{GS}

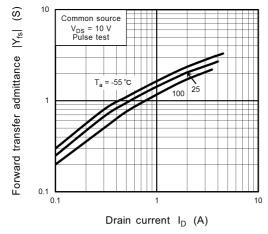


Fig. 8.5 |Y_{fs}| - I_D

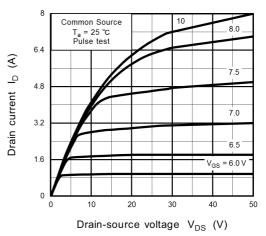


Fig. 8.2 I_D - V_{DS}

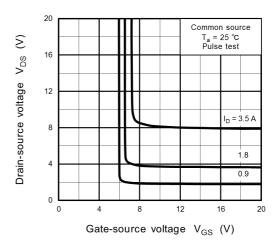


Fig. 8.4 V_{DS} - V_{GS}

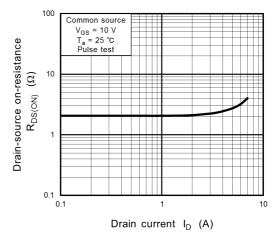


Fig. 8.6 R_{DS(ON)} - I_D

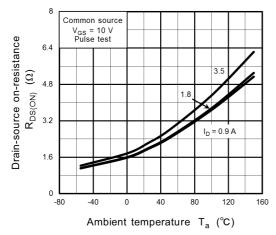


Fig. 8.7 R_{DS(ON)} - T_a

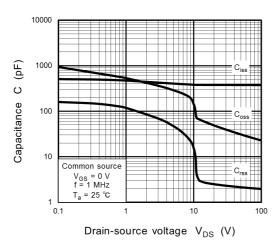


Fig. 8.9 C - V_{DS}

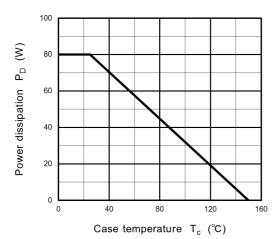


Fig. 8.11 P_D - T_c (Guaranteed Maximum)

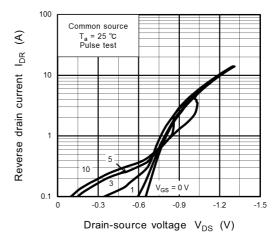


Fig. 8.8 I_{DR} - V_{DS}

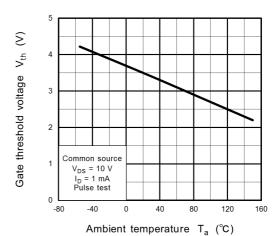


Fig. 8.10 V_{th} - T_a

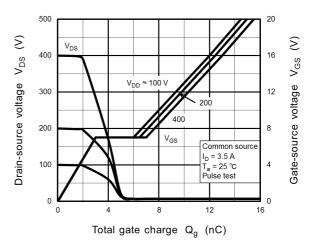


Fig. 8.12 Dynamic Input/Output Characteristics

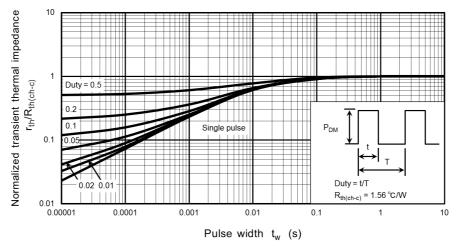


Fig. 8.13 $r_{th}/R_{th(ch-c)} - t_w$ (Guaranteed Maximum)

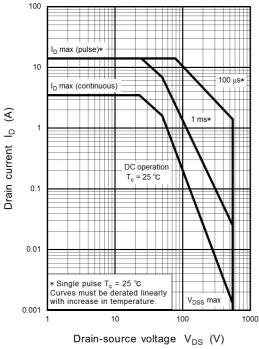


Fig. 8.14 Safe Operating Area (Guaranteed Maximum)

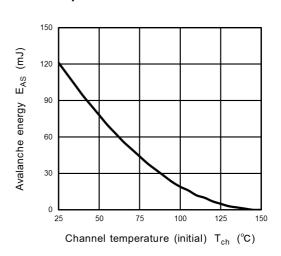


Fig. 8.15 E_{AS} - T_{ch} (Guaranteed Maximum)

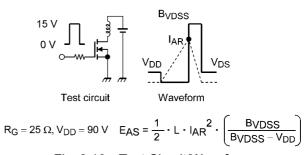


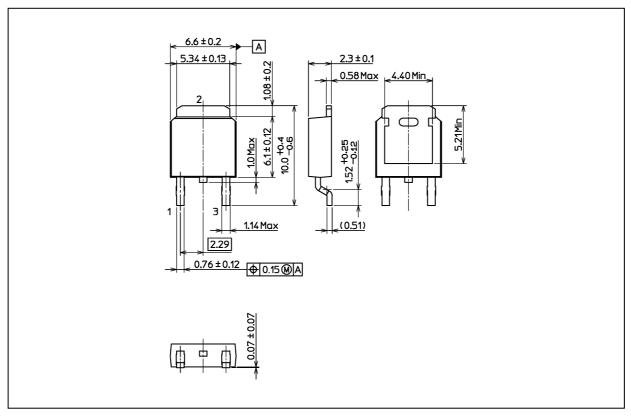
Fig. 8.16 Test Circuit/Waveform

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



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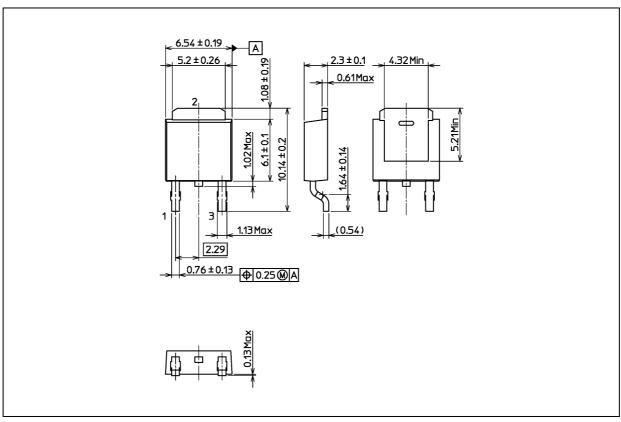
Weight: 0.36 g (typ.)

Package Name(s)	
JEDEC: TO-252	
TOSHIBA: 2-7K1S	
Nickname: DPAK	



Package Dimensions

Unit: mm



Both products are compliant with the JEDEC: TO-252 Package specification. Please contact the Toshiba sales representative for further details.

Weight: 0.389 g (typ.)

Package Name(s)
JEDEC: TO-252
TOSHIBA: 2-7N1S
Nickname: DPAK



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